COMPLIANT HALOGEN FREE





Dual N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
30	0.0165 at V _{GS} = 10 V	8.7		
	0.022 at V _{GS} = 4.5 V	7.5		

SO-8 S1 1 8 D1 G1 2 7 D1 S2 3 6 D2 G2 4 5 D2

Top View

Ordering Information: Si4330DY-T1-E3 (Lead (Pb)-free)

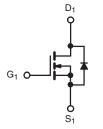
Si4330DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

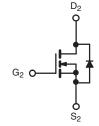
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested

APPLICATIONS

- Notebook
 - Load Switch
 - DC/DC Conversion
 - Auxiliary Voltage





N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	30		V	
Gate-Source Voltage		V_{GS}	± 20			
Continuous Drain Current /T 150 °C\a	T _A = 25 °C	- I _D	8.7	6.6		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		7.0	5.3	Α	
Pulsed Drain Current		I _{DM}	± 30		Α .	
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	0.9		
Mariana Bana Biasia di ad	T _A = 25 °C	- P _D	2.0	1.1	w	
Maximum Power Dissipation ^a	T _A = 70 °C		1.3	0.7		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manipulation to Applicant	t ≤ 10 s	R _{thJA}	45	62.5	°C/W
Maximum Junction-to-Ambient ^a	Steady State		85	110	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	26	35	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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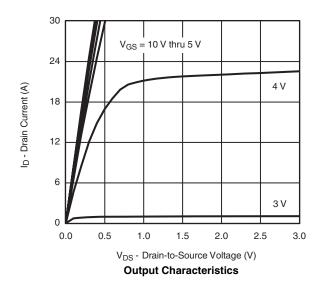
SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Min. Typ.		Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA		
Zero Gate Voltage Drain Current	I _{DSS} -	V _{DS} = 30 V, V _{GS} = 0 V			1			
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 55 °C			5	μΑ		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α		
Drain-Source On-State Resistance ^a	D	$V_{GS} = 10 \text{ V}, I_D = 8.7 \text{ A}$		0.013	0.0165	0		
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 7.5 \text{ A}$		0.018	0.022	Ω		
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 8.7 \text{ A}$		28		S		
Diode Forward Voltage ^a	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V		0.8	1.2	V		
Dynamic ^b								
Total Gate Charge	Q_g			13	20			
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 8.7 \text{ A}$		7.1		nC		
Gate-Drain Charge	Q_{gd}			3.5				
Gate Resistance	R_g		0.5	1	1.7	Ω		
Turn-On Delay Time	t _{d(on)}			10	15			
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω $I_D \cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		10	15	ns		
Turn-Off Delay Time	t _{d(off)}			40	60			
Fall Time	t _f			12	20			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, dl/dt = 100 A/μs		45	70			

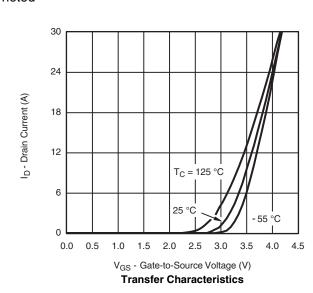
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



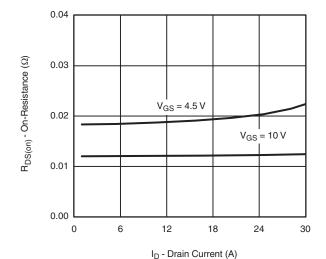




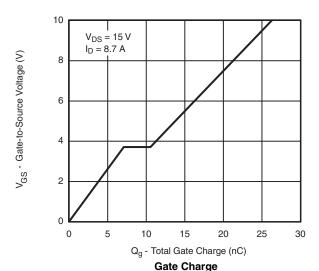




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current



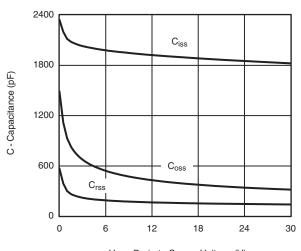
T_J = 150 °C

T_J = 25 °C

T_J = 25 °C

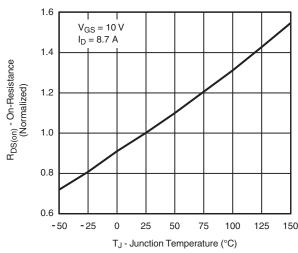
V_{SD} - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

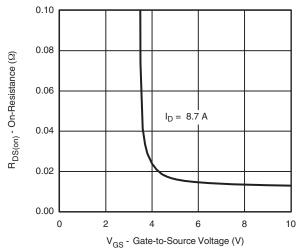


 $V_{\mbox{\footnotesize DS}}$ - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature

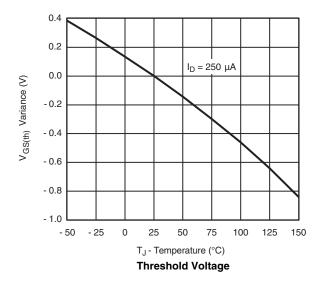


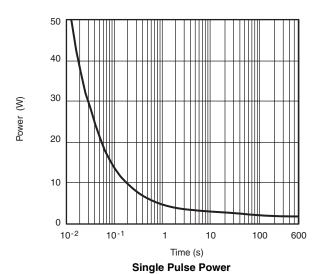
On-Resistance vs. Gate-to-Source Voltage

I_S - Source Current (A)

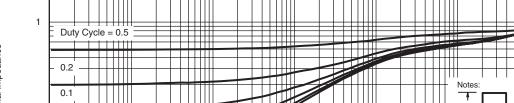
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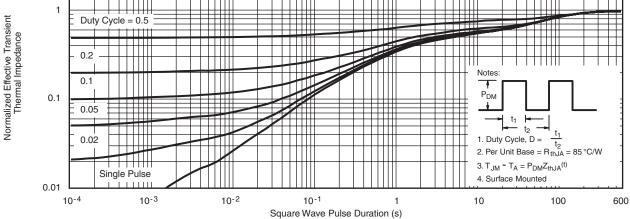
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





100 Limited by R_{DS(on)} 10 I_D - Drain Current (A) P(t) = 0.001P(t) = 0.01P(t) = 0.1T_A = 25 °C P(t) = 10.1 Single Pulse P(t) = 10dc ## **BVDSS Limited** 0.01 0.1 100 V_{DS} - Drain-to-Source Voltage (V) * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified Safe Operating Area



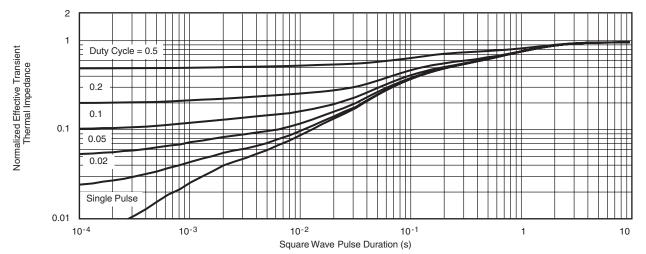


Normalized Thermal Transient Impedance, Junction-to-Ambient

2



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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